

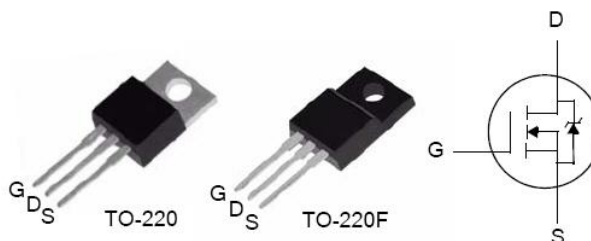
**600V N-Channel MOSFET**
**General Features**

- Low ON Resistance
- Low Gate Charge (typical 38.6nC)
- Fast Switching
- 100% Avalanche Tested
- RoHS Compliant/Lead Free

$BV_{DSS}$	$R_{DS(ON)}$ (Max.)	$I_D$
600V	1.1 $\Omega$	7.0A

**Applications**

- High Efficiency SMPS
- Adaptor/Charger
- Active PFC
- LCD Panel Power


**Ordering Information**

Part Number	Package	Marking
FTP07N60	TO-220	FTP07N60
FTA07N60	TO-220F	FTA07N60

**Absolute Maximum Ratings**
 $T_C=25^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	FTP07N60	FTA07N60	Unit
$V_{DSS}$	Drain-to-Source Voltage <sup>[1]</sup>	600		V
$I_D$	Continuous Drain Current	7.0	7.0*	A
$I_{D@100^{\circ}\text{C}}$	Continuous Drain Current	Figure 3		
$I_{DM}$	Pulsed Drain Current, $V_{GS}@10\text{V}^{[2]}$	Figure 6		
$P_D$	Power Dissipation	139	31	W
	Derating Factor above 25 $^{\circ}\text{C}$	1.1	0.25	W/ $^{\circ}\text{C}$
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$		V
$E_{AS}$	Single Pulse Avalanche Energy $L=20\text{mH}$ , $I_D=7.0\text{A}$	490		mJ
dv/dt	Peak Diode Recovery dv/dt <sup>[3]</sup>	4.5		V/ns
$T_L$	Soldering Temperature	300		$^{\circ}\text{C}$
	Distance of 1.6mm from case for 10 seconds			
$T_J$ and $T_{STG}$	Operating and Storage Temperature Range	-55 to 150		

\*Drain Current limited by Maximum Junction Temperature.

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

**Thermal Characteristics**

Symbol	Parameter	FTP07N60	FTA07N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.9	4.0	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	60	60	



**Electrical Characteristics**

**OFF Characteristics**

T<sub>C</sub> =25°C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	600	--	--	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	--	0.6	--	V/°C	Reference to 25°C, I <sub>D</sub> =250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	--	--	12	μA	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V
		--	--	100		V <sub>DS</sub> =480V, V <sub>GS</sub> =0V, T <sub>C</sub> =125°C
I <sub>GSS</sub>	Gate-to-Source Leakage Current	--	--	100	nA	V <sub>GS</sub> =+30V
		--	--	-100		V <sub>GS</sub> =-30V

**ON Characteristics**

T<sub>C</sub> =25°C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
R <sub>DS(ON)</sub>	Static Drain-to-Source On-Resistance	--	0.9	1.1	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =4.2A <sup>[4]</sup>
V <sub>GS(TH)</sub>	Gate Threshold Voltage	2.0	--	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA
gfs	Forward Transconductance	--	7.5	--	S	V <sub>DS</sub> =15V, I <sub>D</sub> =7.0A <sup>[4]</sup>

**Dynamic Characteristics**

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C <sub>ISS</sub>	Input Capacitance	--	1304	--	pF	V <sub>GS</sub> =0V V <sub>DS</sub> =25V f=1.0MHz Figure 14
C <sub>OSS</sub>	Output Capacitance	--	102	--		
C <sub>RSS</sub>	Reverse Transfer Capacitance	--	20	--		
Q <sub>G</sub>	Total Gate Charge	--	38.6	--	nC	V <sub>DD</sub> =300V I <sub>D</sub> =7.0A Figure 15
Q <sub>GS</sub>	Gate-to-Source Charge	--	5.5	--		
Q <sub>GD</sub>	Gate-to-Drain (Miller) Charge	--	18	--		

**Resistive Switching Characteristics**

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
t <sub>d(ON)</sub>	Turn-on Delay Time	--	32	--	ns	V <sub>DD</sub> =300V I <sub>D</sub> =7.0A V <sub>GS</sub> =10V R <sub>G</sub> =20Ω
t <sub>rise</sub>	Rise Time	--	86	--		
t <sub>d(OFF)</sub>	Turn-off Delay Time	--	87	--		
t <sub>fall</sub>	Fall Time	--	57	--		

**Source-Drain Diode Characteristics**
 $T_C=25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
$I_{SD}$	Continuous Source Current (Body Diode)	--	--	7.0	A	Integral P-N diode in MOSFET
$I_{SM}$	Maximum Pulsed Current (Body Diode)	--	--	28	A	
$V_{SD}$	Diode Forward Voltage	--	--	1.2	V	$I_S=7.0\text{A}$ , $V_{GS}=0\text{V}$
$t_{rr}$	Reverse Recovery Time	--	311	--	ns	$V_{GS}=0\text{V}$ $I_F=7.0\text{A}$ , $di/dt=100\text{A}/\mu\text{s}$
$Q_{rr}$	Reverse Recovery Charge	--	2200	--	nC	

**NOTE:**

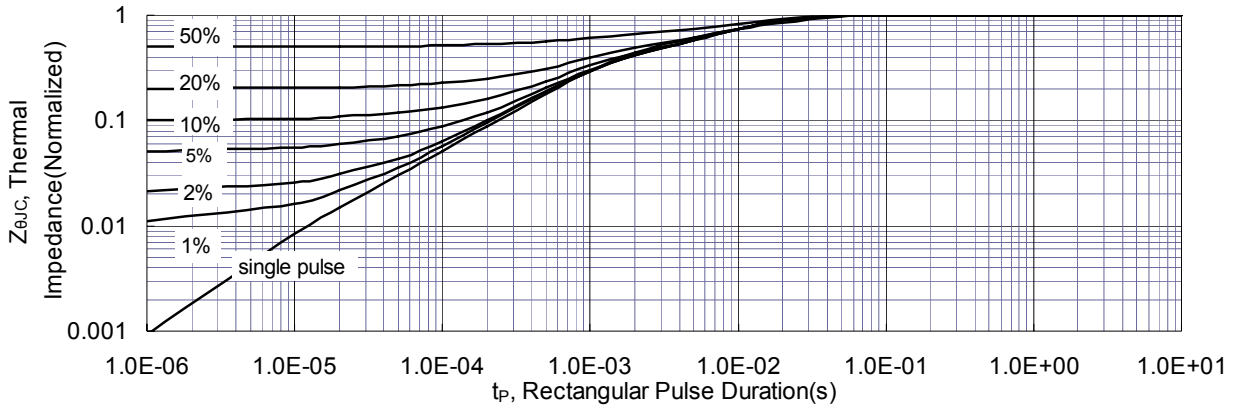
[1]  $T_J=+25^\circ\text{C}$  to  $+150^\circ\text{C}$

[2] Repetitive rating, pulse width limited by maximum junction temperature.

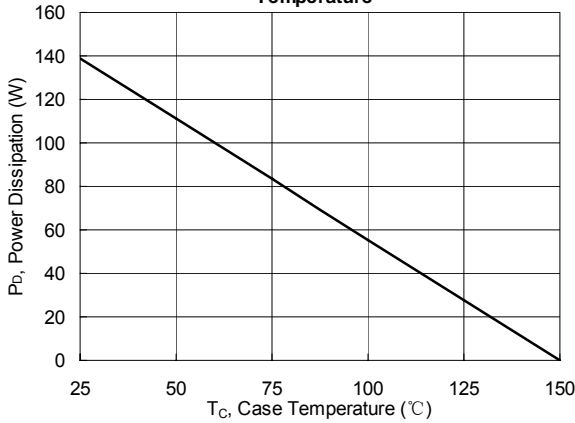
[3]  $I_{SD}=7.0\text{A}$ ,  $di/dt \leq 100\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ ,  $T_J=+150^\circ\text{C}$

[4] Pulse width  $\leq 380\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

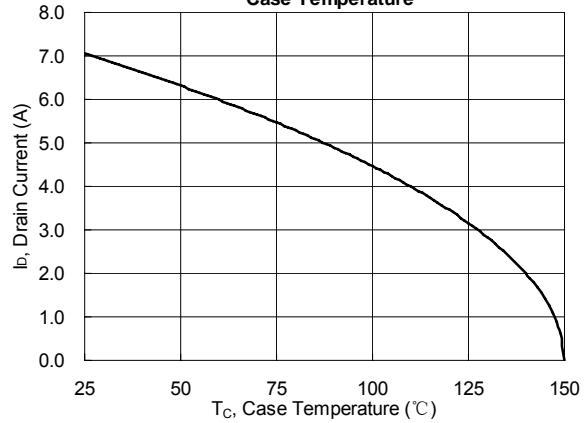
**Figure 1. Maximum Effective Thermal Impedance, Junction-to-Case**



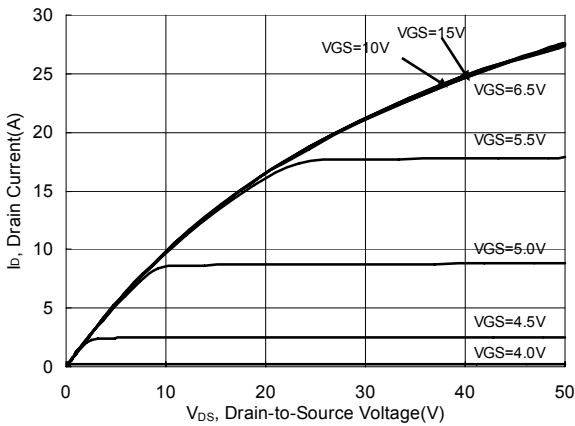
**Figure 2. Maximum Power Dissipation vs. Case Temperature**



**Figure 3. Maximum Continuous Drain Current vs Case Temperature**



**Figure 4. Typical Output Characteristics**



**Figure 5. Typical Drain-to-Source ON Resistance vs. Gate Voltage and Drain Current**

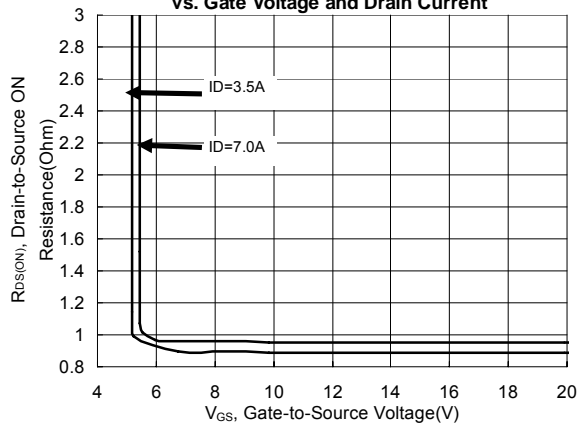


Figure 6. Maximum Peak Current Capability

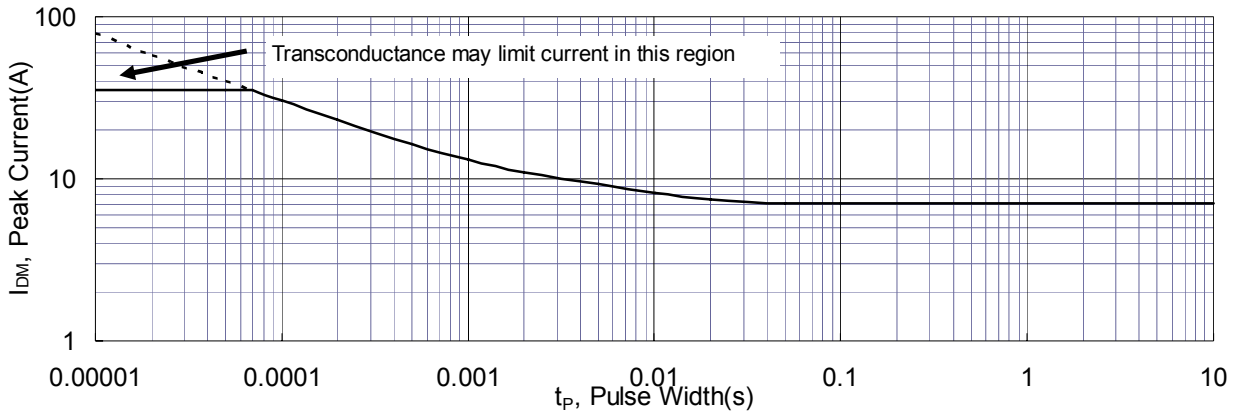


Figure 7. Typical Transfer Characteristics

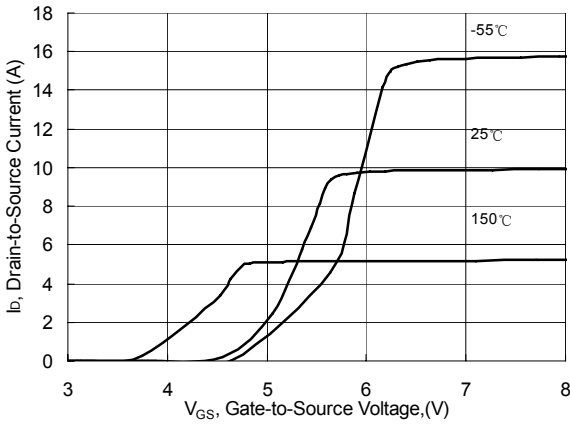


Figure 8. Unclamped Inductive Switching Capability

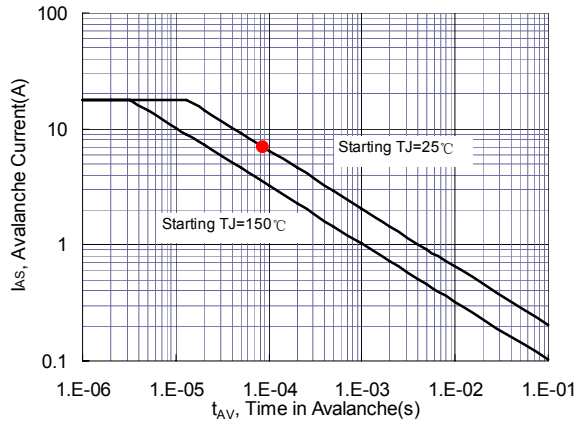


Figure 9. Typical Drain-to-Source ON Resistance

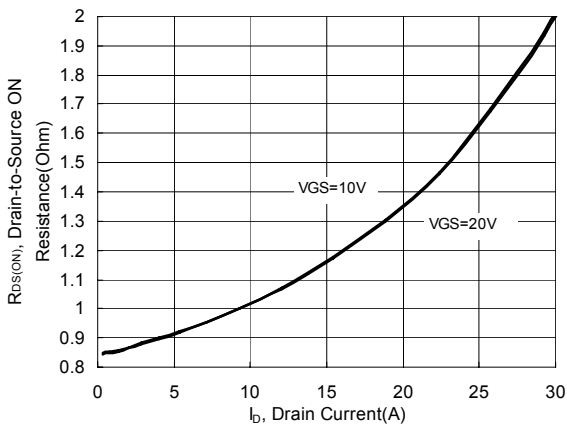
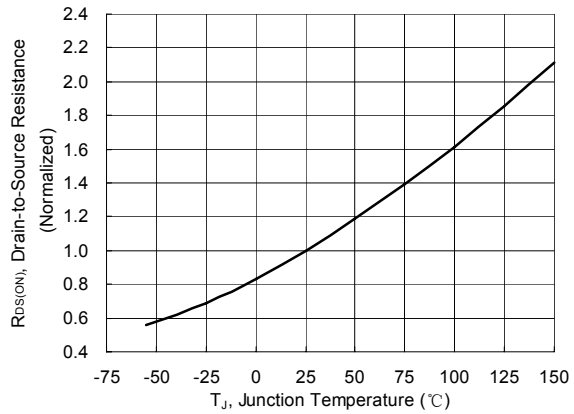
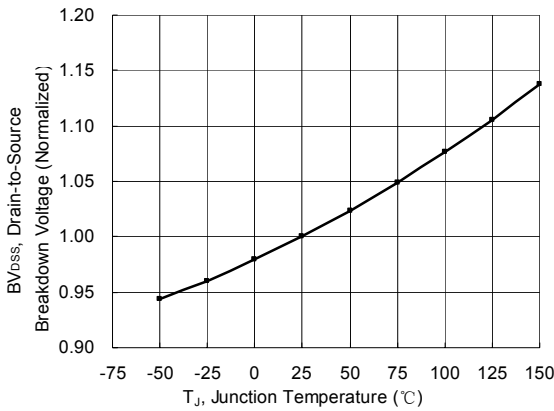


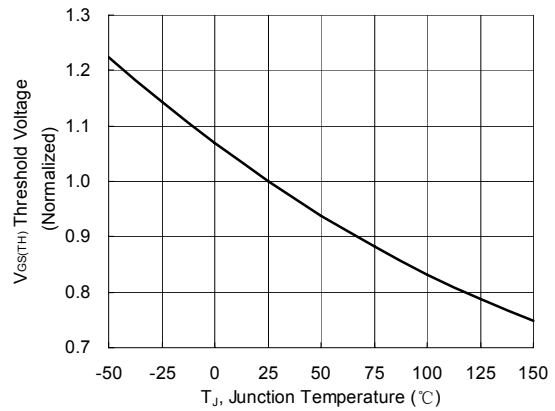
Figure 10. Typical Drain-to-Source On Resistance vs. Junction Temperature



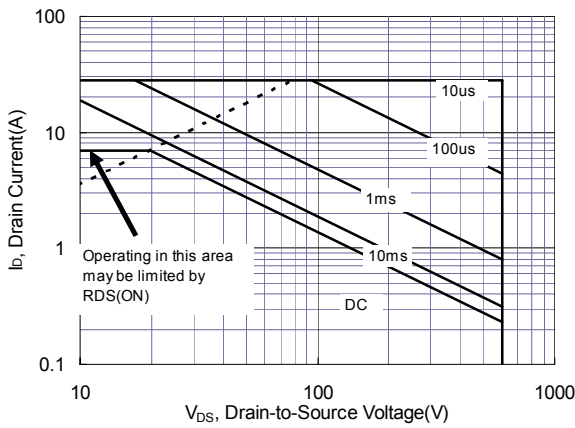
**Figure 11. Typical Breakdown Voltage vs. Junction Temperature**



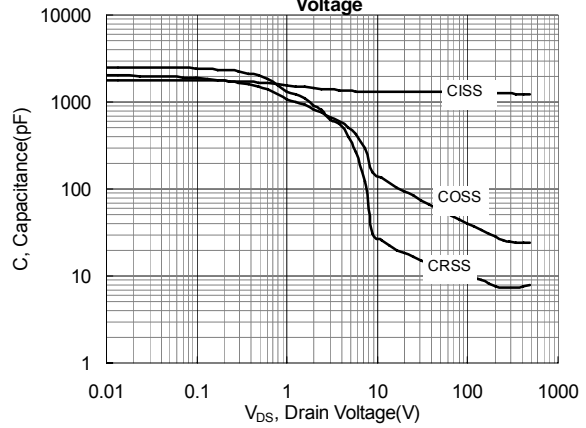
**Figure 12. Typical Threshold Voltage vs. Junction Temperature**



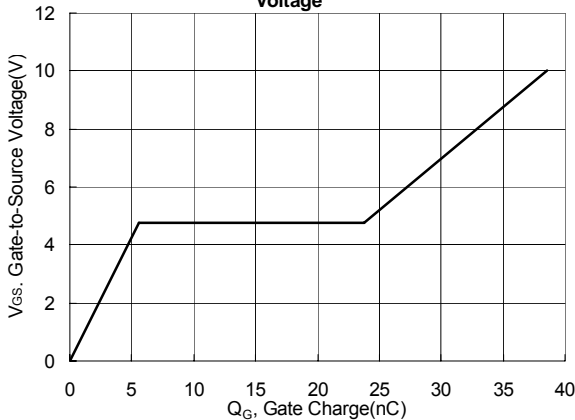
**Figure 13. Maximum Forward Safe Operation Area**



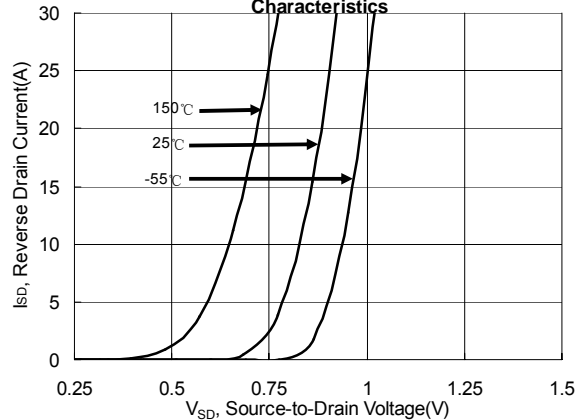
**Figure 14. Typical Capacitance vs. Drain-to-Source Voltage**



**Figure 15. Typical Gate Charge vs. Gate-to-Source Voltage**



**Figure 16. Typical Body Diode Transfer Characteristics**



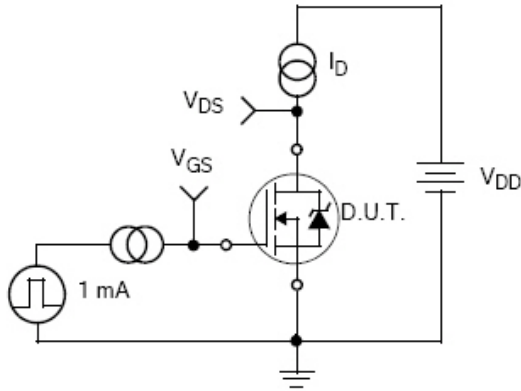
**Test Circuit**


Figure 17. Gate Charge Test Circuit

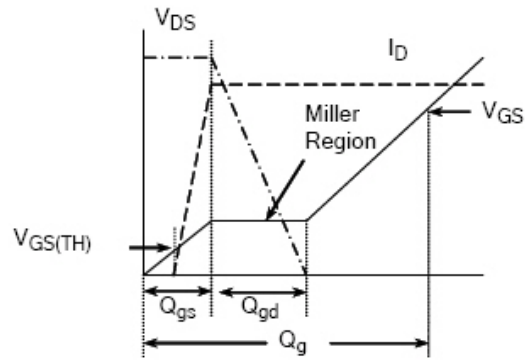


Figure 18. Gate Charge Waveform

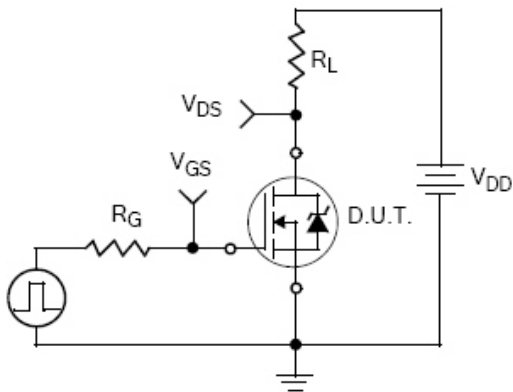


Figure 19. Resistive Switching Test Circuit

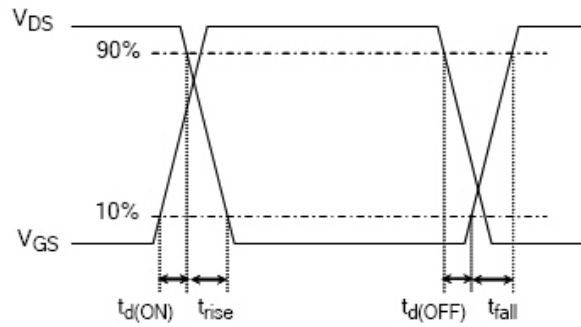


Figure 20. Resistive Switching Waveforms

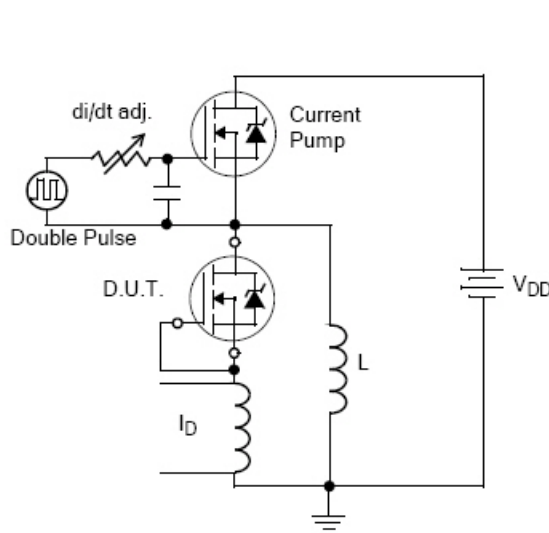


Figure 21. Diode Reverse Recovery Test Circuit

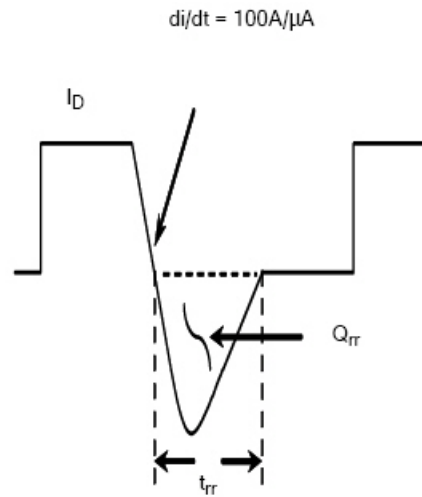


Figure 22. Diode Reverse Recovery Waveform

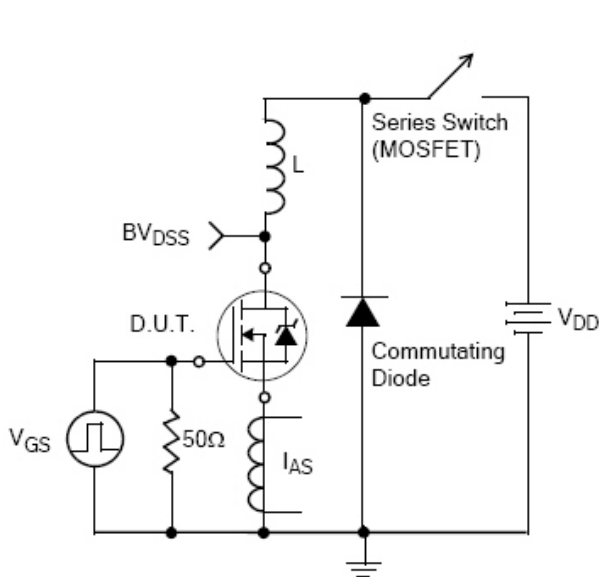


Figure 23. Unclamped Inductive Switching Test Circuit

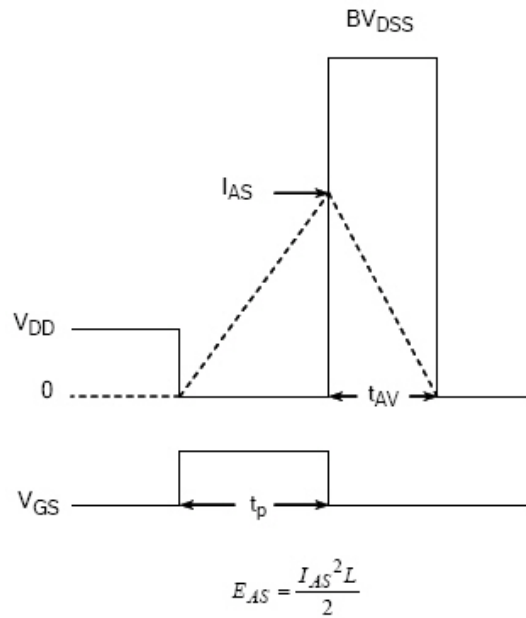
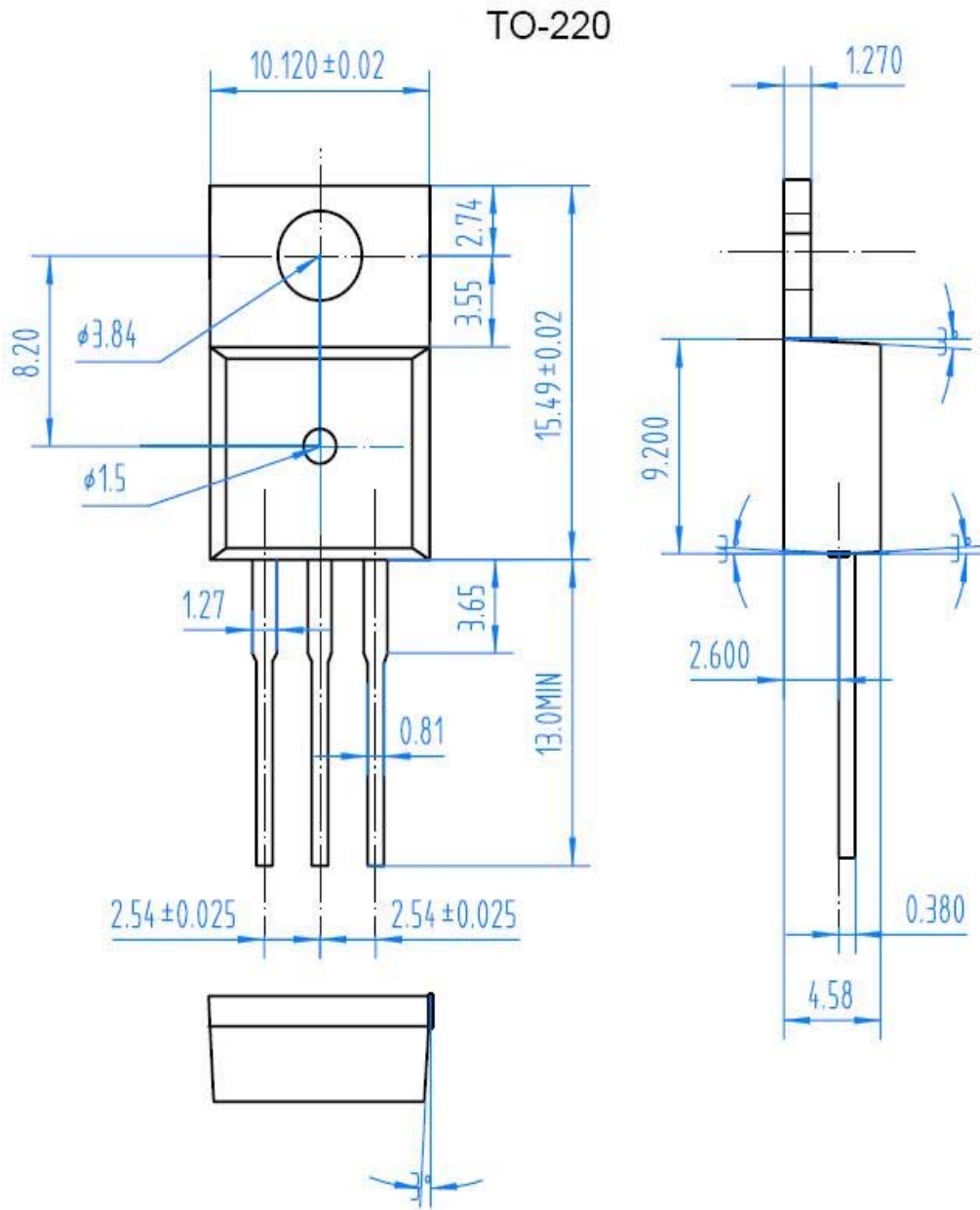
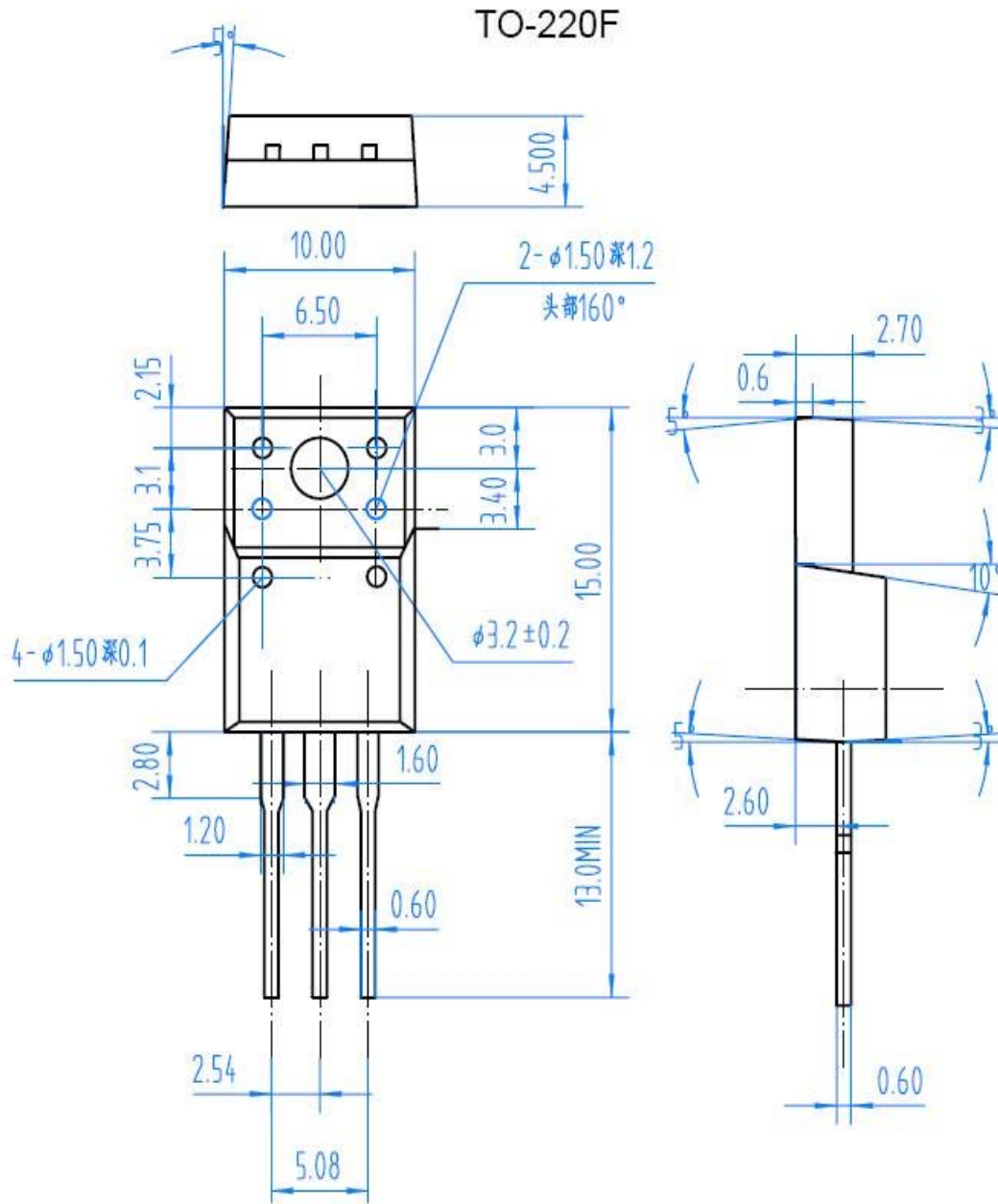


Figure 24. Unclamped Inductive Switching Waveforms



**Package Dimensions**






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